Product Overview

FDD8896: PowerTrench® MOSFET, N-Channel, 30V, 94A, 4.7mΩ

For complete documentation, see the data sheet.

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(ON)}$ and fast switching speed.

Features

- $R_{DS(ON)}$ = 5.7 mΩ , V_{GS} = 10V, I_D = 35V
- $R_{DS(ON)}$ = 6.8 mΩ , V_{GS} = 4.5V, I_D = 35V
- High performance trench technology for extremely low $R_{DS(ON)}$
- Low gate charge
- High power and current handling capability

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{(BR)DSS}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ V_{GS} = 2.5 V (mΩ)	$R_{DS(on)}$ Max @ V_{GS} = 4.5 V (mΩ)	$R_{DS(on)}$ Max @ V_{GS} = 10 V (mΩ)	Q_g Typ @ V_{GS} = 4.5 V (nC)	Q_g Typ @ V_{GS} = 10 V (nC)	C_{iss} Typ (pF)	Package Type
FDD8896	Pb-free Halide free	Active	N-Channel	Single	30	20	2.5	94	80	-	6.8	5.7	-	24	2525	DPAK-3 / TO-252-3

For more information please contact your local sales support at www.onsemi.com.

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